

# 60 V, 7 A NPN low VCEsat (BISS) transistor Rev. 2 — 8 August 2012

Product data sheet

#### **Product profile** 1.

### 1.1 General description

NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4041PZ.

### 1.2 Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FF</sub>) at high I<sub>C</sub>

### 1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management

1.4 Quick reference data

- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required PCB area than for conventional transistors
- Charging circuits
- Power switches (e.g. motors, fans)

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	60	V
I <sub>C</sub>	collector current		-	-	7	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	15	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C = 6$ A; $I_B = 600$ mA; pulsed; $t_p \le 300$ μs; δ $\le 0.02$ ; $T_{amb} = 25$ °C	-	17.5	25	mΩ



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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector		C I
3	E	emitter		в
4	С	collector		
			SOT223 (SC-73)	E sym123

# 3. Ordering information

Table 3. Ordering information					
Type number Package					
	Name	Description	Version		
PBSS4041NZ	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

### 4. Marking

Table 4.   Marking codes	
Type number	Marking code
PBSS4041NZ	PB4041NZ

# 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	7	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	15	А
I <sub>B</sub>	base current			-	1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	770	mW
			[2]	-	1700	mW
			[3]	-	2600	mW

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#### Table 5. Limiting values ...continued

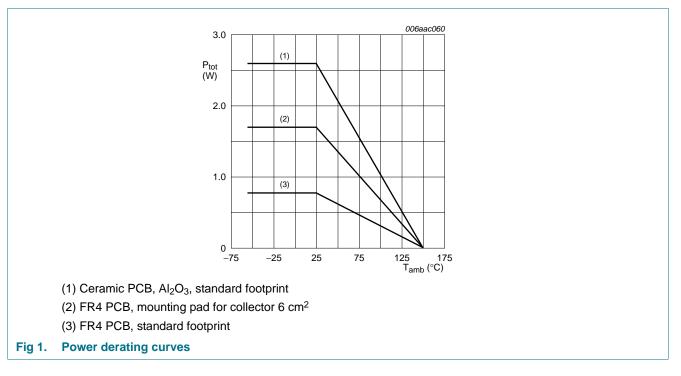
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	150	°C
T <sub>stg</sub>	storage temperature		-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.



### 6. Thermal characteristics

#### Table 6.Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from	thermal resistance	in free air	<u>[1]</u>	-	-	160	K/W
	from junction to ambient		[2] -	-	-	75	K/W
	ampient		[3]	-	-	50	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	11	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

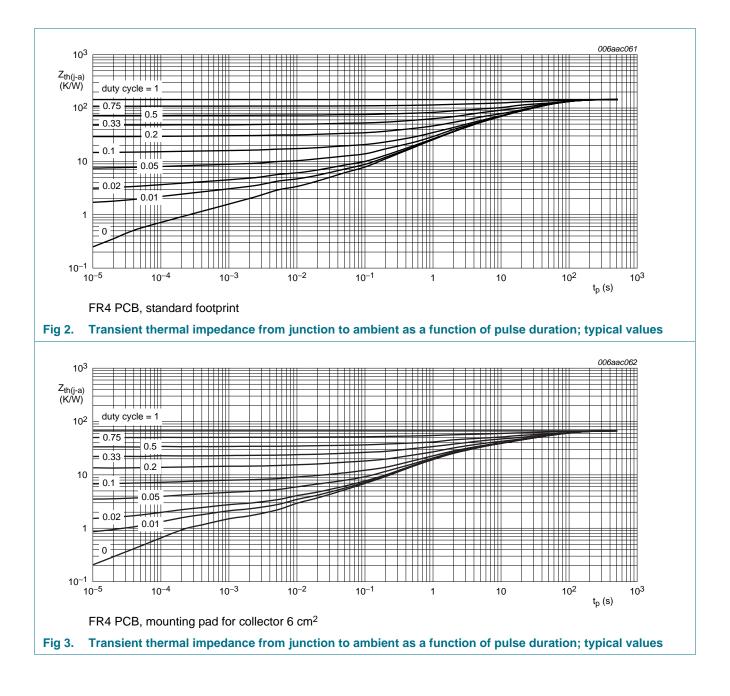
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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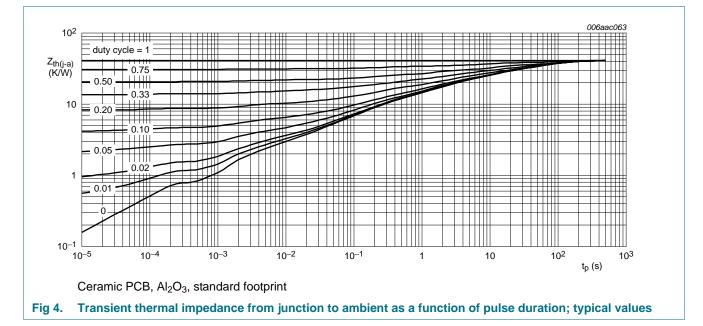
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## 7. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Tun	Mox	Unit
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = 60 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
	current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = 48 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}; \text{ T}_{amb} = 25 ^{\circ}\text{C}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$ \begin{array}{l} V_{CE} = 2 \ V; \ I_{C} = 500 \ mA; \ pulsed; \\ t_{p} \leq 300 \ \mus; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array} $	300	500	-	
		$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \ V; \ I_C = 1 \ A; \ pulsed; \ t_p \leq 300 \ \mu s; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ C \end{array}$	300	500	-	
		$ \begin{aligned} &V_{CE} = 2 \text{ V; } I_C = 2 \text{ A; pulsed; } t_p \leq 300  \mu\text{s;} \\ &\delta \leq 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C} \end{aligned} $	300	500	-	
		$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \ V; \ I_C = 4 \ A; \ pulsed; \ t_p \leq 300 \ \mu s; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ C \end{array}$	250	400	-	
		$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \ V; \ I_C = 6 \ A; \ pulsed; \ t_p \leq 300 \ \mu s; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ C \end{array}$	100	200	-	
		$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \ V; \ I_C = 7 \ A; \ pulsed; \ t_p \leq 300 \ \mu s; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ C \end{array}$	50	100	-	

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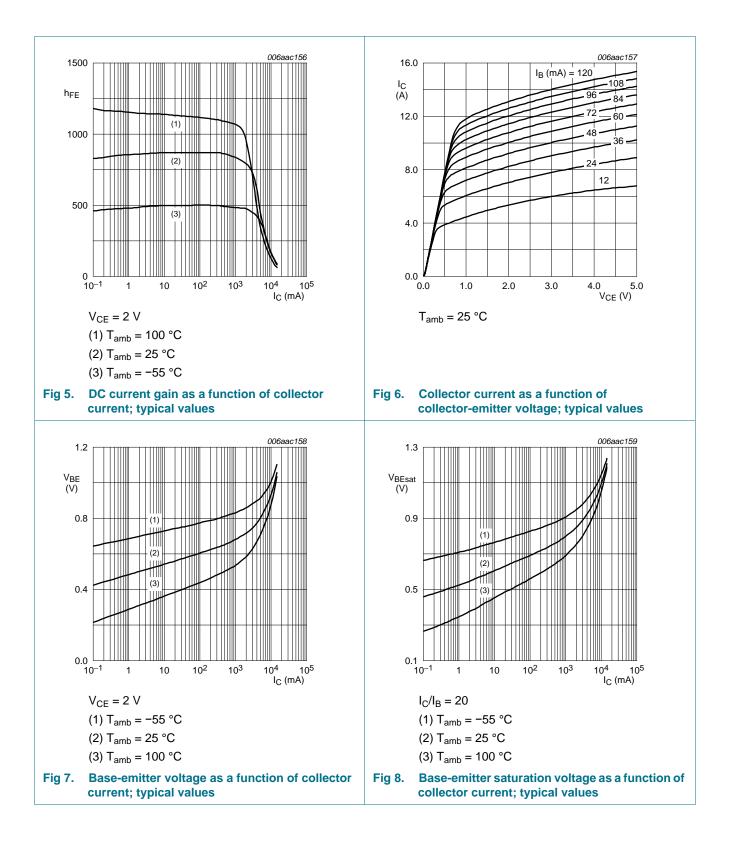
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	25	35	mV
		$    I_C = 1 \text{ A}; I_B = 10 \text{ mA}; \text{ pulsed};                                    $	-	43	60	mV
		$    I_C = 2 \text{ A}; I_B = 40 \text{ mA}; \text{ pulsed};                                    $	-	53	75	mV
		$    I_C = 4 \text{ A}; I_B = 200 \text{ mA}; \text{ pulsed};                                    $	-	78	110	mV
		$    I_C = 4 \text{ A}; I_B = 40 \text{ mA}; \text{ pulsed};                                    $	-	115	160	mV
		$    I_C = 7 \text{ A}; I_B = 350 \text{ mA}; \text{ pulsed};                                    $	-	130	195	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$    I_C = 6 \text{ A}; I_B = 600 \text{ mA}; \text{ pulsed};                                    $	-	17.5	25	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$    I_C = 1 \text{ A}; I_B = 100 \text{ mA}; \text{ pulsed};                                    $	-	0.83	0.9	V
		$    I_C = 4 \text{ A}; I_B = 400 \text{ mA}; \text{ pulsed};                                    $	-	0.98	1.05	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \text{ V; } I_C = 2 \text{ A; pulsed; } t_p \leq 300  \mu\text{s;} \\ \delta \leq 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C} \end{array}$	-	0.72	0.85	V
t <sub>d</sub>	delay time	$V_{CC}$ = 12.5 V; I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.05 A;	-	55	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.05 A; T <sub>amb</sub> = 25 °C	-	55	-	ns
t <sub>on</sub>	turn-on time		-	110	-	ns
t <sub>s</sub>	storage time		-	1220	-	ns
t <sub>f</sub>	fall time		-	230	-	ns
t <sub>off</sub>	turn-off time		-	1450	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; I <sub>C</sub> = 100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	105	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	50	-	pF

### Table 7. Characteristics ...continued

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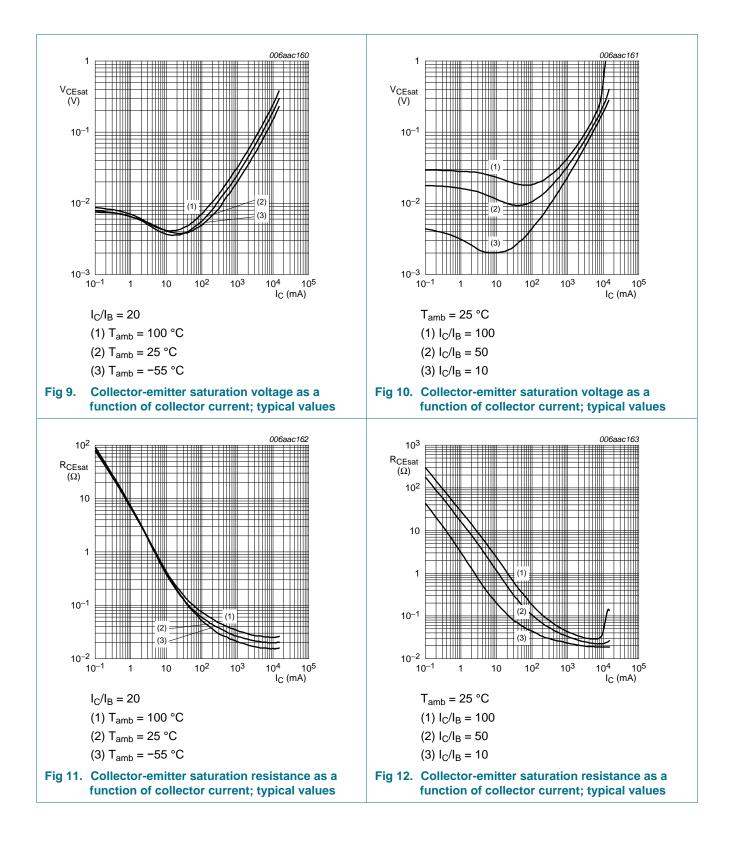
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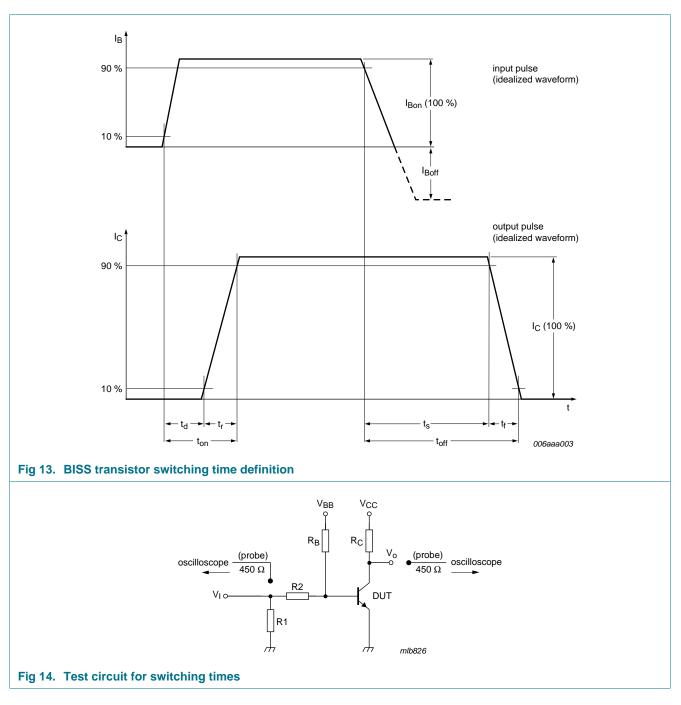


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### 8. Test information



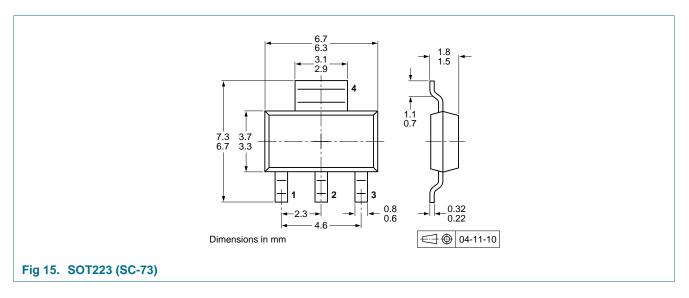
### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard*Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

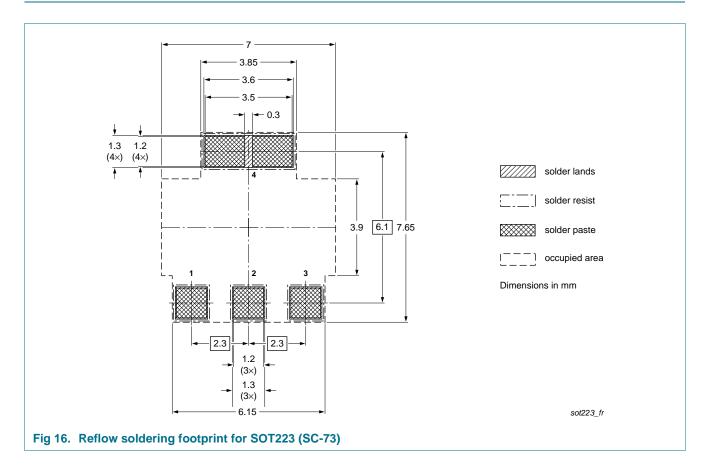
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### 9. Package outline



# 10. Soldering

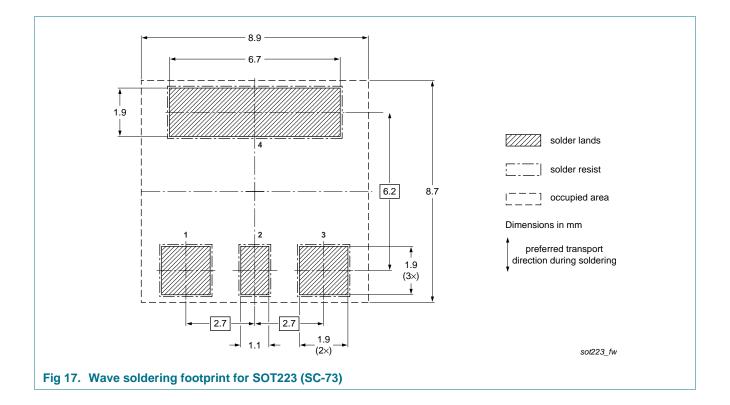


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# **11. Revision history**

Table 8. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4041NZ v.2	20120808	Product data sheet	-	PBSS4041NZ v.1
Modifications:		stics": V <sub>CEsat</sub> corrected		
PBSS4041NZ v.1	20100331	Product data sheet	-	-

#### 60 V, 7 A NPN low VCEsat (BISS) transistor

### **12. Legal information**

### **12.1 Data sheet status**

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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